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(71) Applicant: MITSUBISHI ELECTRIC CORP

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(74) Representative:

(54) PRODUCTION FOR
SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To shorten a working hour which is long time (about 2 hours) in the conventional method, when producing an electrode for semiconductor element.

CONSTITUTION: A plating solution 5 is blown to a wafer 1, on which the semiconductor element is formed, and when current is applied between a cathode electrode 13 opposite to the wafer 1 and a current regulating anode electrode 8 to form the element electrode, high, low and reverse current are applied repeatedly from a current control type D.C. power source 10.

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